

ABSTRACT OF THE DISCLOSURE

In a semiconductor laser device including having an index-guided structure and oscillating in a fundamental transverse mode, a lower cladding layer, a lower optical waveguide layer, a quantum well layer, an upper optical waveguide layer, and a current confinement structure are formed in this order. The thickness of the upper optical waveguide layer is smaller than the thickness of the lower optical waveguide layer. In addition, the sum of the thicknesses of the upper and lower optical waveguide layers may be 0.5 micrometers or greater. Further, the distance between the bottom of the current confinement structure and the upper surface of the quantum well layer may be smaller than 0.25 micrometers.